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FDN337N

N-Channel Logic Level Enhancement Mode Field Effect Transistor

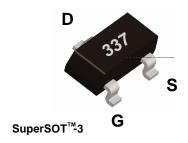
General Description

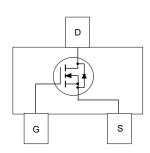
SuperSOT™-3 N-Channel logic level enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage applications in notebook computers, portable phones, PCMCIA cards, and other battery powered circuits where fast switching, and low in-line power loss are needed in a very small outline surface mount package.

Features

- Industry standard outline SOT-23 surface mount package using proprietary SuperSOT[™]-3 design for superior thermal and electrical capabilities.
- High density cell design for extremely low R_{DS(ON)}.
- Exceptional on-resistance and maximum DC current capability.







Absolute Maximum Ratings T. = 25°C unless other wise noted

Symbol	Parameter		FDN337N	Units
V _{DSS}	Drain-Source Voltage		30	V
/ _{GSS}	Gate-Source Voltage - Continuous		±8	V
I _D	Drain/Output Current - Continuous		2.2	А
	- Pulsed		10	
P _D	Maximum Power Dissipation	(Note 1a)	0.5	W
		(Note 1b)	0.46	
T_J , T_{STG}	Operating and Storage Temperature R	ange	-55 to 150	°C
HERMA	L CHARACTERISTICS			·
R _{OJA}	Thermal Resistance, Junction-to-Ambient (Note 1a)		250	°C/W
R _{θJC}	Thermal Resistance, Junction-to-Case	(Note 1)	75	°C/W

Symbol	Parameter	Conditions		Min	Тур	Max	Units
OFF CHAR	ACTERISTICS				•		
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$		30			V
$\Delta BV_{DSS}/\Delta T_{J}$	Breakdown Voltage Temp. Coefficient	$I_D = 250 \mu A$, Referenced to	25 °C		41		mV/°C
DSS	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, \ V_{GS} = 0 \text{ V}$				1	μΑ
			$T_J = 55^{\circ}C$			10	μA
GSSF	Gate - Body Leakage, Forward	$V_{GS} = 8 \text{ V}, V_{DS} = 0 \text{ V}$	'			100	nA
GSSR	Gate - Body Leakage, Reverse	$V_{GS} = -8 \text{ V}, V_{DS} = 0 \text{ V}$				-100	nA
ON CHARA	CTERISTICS (Note)						
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$		0.4	0.7	1	V
$\Delta V_{GS(th)}/\Delta T_{J}$	Gate Threshold Voltage Temp. Coefficient	$I_D = 250 \mu A$, Referenced to	25 °C		-2.3		mV/°C
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = 4.5 \text{ V}, I_{D} = 2.2 \text{ A}$			0.054	0.065	Ω
,			T _J =125°C		0.08	0.11	
		$V_{GS} = 2.5 \text{ V}, I_{D} = 2 \text{ A}$			0.07	0.082	
D(ON)	On-State Drain Current	$V_{GS} = 4.5 \text{ V}, \ V_{DS} = 5 \text{ V}$		10			Α
9 _{FS}	Forward Transconductance	$V_{DS} = 5 \text{ V}, I_{D} = 2.2 \text{ A}$			13		S
DYNAMIC (HARACTERISTICS						
C _{iss}	Input Capacitance	$V_{DS} = 10 \text{ V}, \ V_{GS} = 0 \text{ V},$ f = 1.0 MHz			300		pF
C _{oss}	Output Capacitance				145		pF
C _{rss}	Reverse Transfer Capacitance				35		pF
SWITCHING	CHARACTERISTICS (Note)						
D(on)	Turn - On Delay Time	$V_{DD} = 5 \text{ V}, \ I_{D} = 1 \text{ A}, \ V_{GS} = 4.5 \text{ V}, \ R_{GEN} = 6 \Omega$			4	10	ns
r	Turn - On Rise Time				10	18	ns
D(off)	Turn - Off Delay Time				17	28	ns
f	Turn - Off Fall Time				4	10	ns
Q_g	Total Gate Charge	$V_{DS} = 10 \text{ V}, I_{D} = 2.2 \text{ A},$ $V_{GS} = 4.5 \text{ V}$			7	9	nC
Q_{gs}	Gate-Source Charge				1.1		nC
Q_{gd}	Gate-Drain Charge				1.9		nC
DRAIN-SO	JRCE DIODE CHARACTERISTICS AND	MAXIMUM RATINGS		1	ı	ı	
l _s	Maximum Continuous Drain-Source Diode Forward Current				0.42	Α	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = 0.42 \text{ A} \text{ (Note)}$)		0.65	1.2	V

Note

Typical $R_{_{\theta, \text{M}}}$ using the board layouts shown below on FR-4 PCB in a still air environment :

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2.0%.



a. 250°C/W when mounted on 0.02 in² pad of 2oz Cu.



b. 270°C/W when mounted on a 0.001 in² pad of 2oz Cu.

^{1.} R_{gus} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{guc} is guaranteed by design while R_{gcs} is determined by the user's board design.

Typical Electrical Characteristics

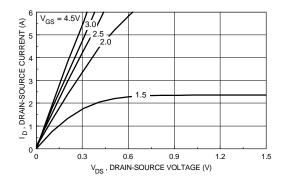


Figure 1. On-Region Characteristics.

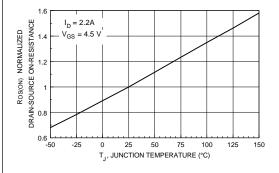


Figure 3. On-Resistance Variation with Temperature.

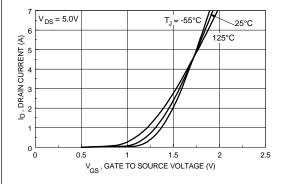


Figure 5. Transfer Characteristics.

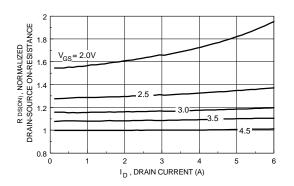


Figure 2. On-Resistance Variation with Drain Current and Gate

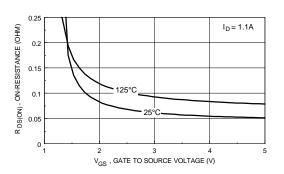
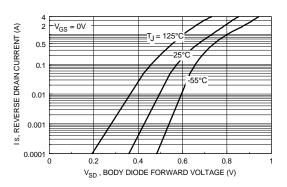


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.



Typical Electrical Characteristics (continued)

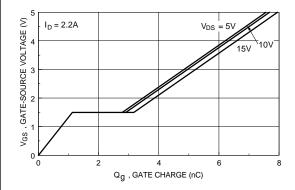


Figure 7. Gate Charge Characteristics.

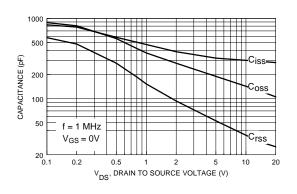


Figure 8. Capacitance Characteristics.

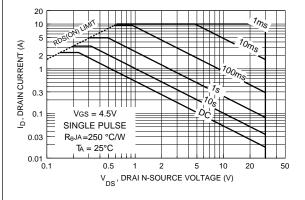


Figure 9. Maximum Safe Operating Area.

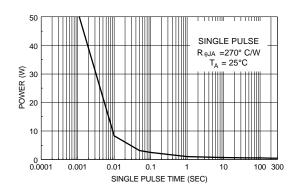


Figure 10. Single Pulse Maximum Power Dissipation.

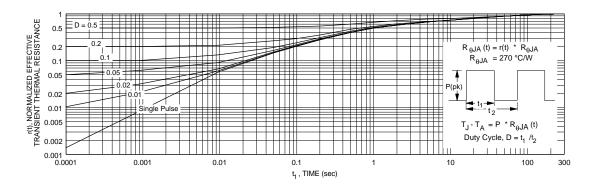


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in note 1b. Transient thermal response will change depending on the circuit board design.

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